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RFMD(R) Expands Broadband Transmission Product Portfolio

World's First 1.2GHz CATV Amplifiers Enable Enhanced, Bandwidth-Driven CATV Services

KOLN, Germany, May 4, 2010 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance RF components and compound semiconductor technologies, today announced the industry's first 1.2 GHz broadband transmission products, enabling enhanced, bandwidth-driven services for CATV operators and their subscribers. The new products provide options for cable operators to upgrade their network infrastructure to 1.2GHz, enhancing their network performance and providing bandwidth for growing broadcast and narrowcast services such as HDTV and emerging 3D HDTV.

The new products include the RFPD2580, the RFPP2590, and the RFOS601x. The RFPD2580 is a power doubler amplifier that uses RFMD's GaN technology to achieve 22.5dB gain at 1.2GHz and best-in-class signal output capability. The RFPP2590 is a hybrid push-pull amplifier module that delivers extremely low distortion and consumes just 240mA from a 24V supply. The RFPP2590 is a companion part to the RFPD2580, and the two products combine to optimize performance in CATV line extender amplifiers deployed in CATV distribution networks.

The RFOS601x is an optical receiver module designed for use in hybrid fiber coax (HFC) optical nodes. Optical nodes reside at the edge of the fiber network, converting light into electrical signals for transmission to CATV set-top boxes and home routers. The low distortion of the RFOS601x enables "fiber-deep" networks, in which the optical network is extended closer to the CATV subscriber, supporting higher data rates and addressing the increasing demand for high bandwidth video and broadband services.

Technical features of the RFPD2580 include:

- 45-1200MHz bandwidth
- 22.5dB minimum gain at 1200MHz
- Power consumption 450mA maximum at 24VDC
- GaN technology
- Best in class output capability

Technical features of the RFPP2590 include:

- 45-1200MHz bandwidth
- 23.0dB minimum gain at 1200MHz
- Power consumption 240mA maximum at 24VDC
- 0.8dB gain flatness
- Extremely low distortion: CTB = -60dBc max, CSO = -65dBc max

Technical features of the RFOS601x include:

- 45-1200MHz bandwidth
- 6.3 pA/sqr(Hz) maximum at 1200MHz EINC
- Typically 32dBA/W O/E at 1200MHz
- Available with FC/APC (RFOS6012) or SC/APC (RFOS6013) optical connector

The RFPD2580, RFPP2590, and RFOS601x are all available in industry-standard SOT115J packages and are available for sampling immediately.

About RFMD's GaN Technology

RFMD is the first to introduce GaN technology in CATV Hybrids. The unique performance characteristics of RFMD's GaN technology allow CATV operators to achieve 3dB higher output power without an increase in current consumption, or a 20% reduction in current consumption without a decrease in output power. RFMD's GaN technology also helps carriers expand the utilization of their cable networks to better compete with satellite and fiber-to-the-home (FTTH) networks.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, variability in operating results, the rate of growth and development of wireless markets, risks associated with the reduced investment in our wireless systems business, our ability to execute on our plans to consolidate or relocate manufacturing operations, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, assembly facility and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, dependence on gallium arsenide (GaAs) for the majority of our products, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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